Data Sheet | December 1992 | File Number 3309

CMOS Quad True/Complement Buffer

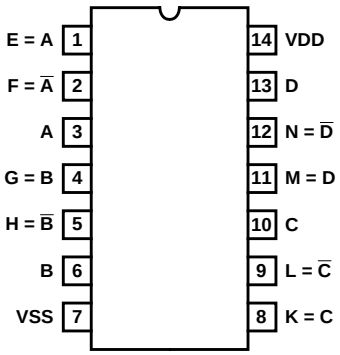
CD4041UBMS types are quad true/complement buffers consisting of n- and p- channel units having low channel resistance and high current (sourcing and sinking) capability. The CD4041UBMS is intended for use as a buffer, line driver, or CMOS-to-TTL driver. It can be used as an ultra-low power resistor-network driver for A/D and D/A conversion, as a transmission-line driver, and in other applications where high noise immunity and low power dissipation are primary design requirements.

The CD4041UBMS is supplied in these 14 lead outline packages:

Braze Seal DIP	H4Q
Frit Seal DIP	H1B
Ceramic Flatpack	H3W

Pinout

CD4041UBMS
TOP VIEW



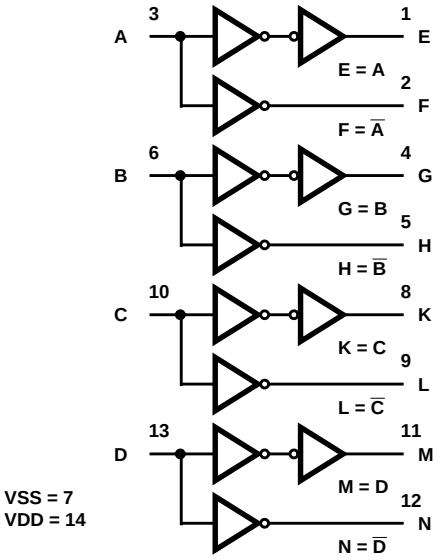
Features

- **High Voltage Type (20V Rating)**
- **Balanced Sink and Source Current; Approximately 4 Times Standard "B" Drive**
- **Equalized Delay to True and Complement Outputs**
- **100% Tested for Quiescent Current at 20V**
- **Maximum Input Current of 1μA at 18V Over Full Package-Temperature Range;**
  - **100nA at 18V and +25°C**
- **5V, 10V and 15V Parametric Ratings**
- **Meets All Requirements of JEDEC Tentative Standard No. 13B, "Standard Specificationsfor Description of 'B' Series CMOS Devices"**

Applications

- **High Current Source/Sink Driver**
- **CMOS-to-DTL/TTL Converter Buffer**
- **Display Driver**
- **MOS Clock Driver**
- **Resistor Network Driver (Ladder or Weighted R)**
- **Buffer**
- **Transmission Line Driver**

Functional Diagram



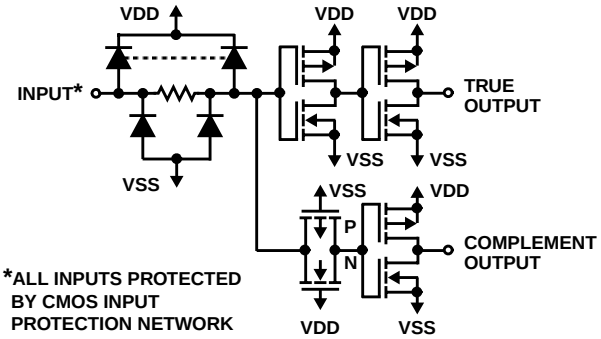


FIGURE 1. SCHEMATIC DIAGRAM 1 OF 4 BUFFERS

Absolute Maximum Ratings

DC Supply Voltage Range, (VDD) . . . . . -0.5V to +20V
(Voltage Referenced to VSS Terminals)
Input Voltage Range, All Inputs . . . . . -0.5V to VDD +0.5V
DC Input Current, Any One Input. . . . . ±10mA
Operating Temperature Range . . . . . -55^oC to $+125^oC$
Package Types D, F, K, H
Storage Temperature Range (TSTG). . . . . -65^oC to $+150^oC$
Lead Temperature (During Soldering) . . . . . $+265^oC$
At Distance 1/16 ± 1/32 Inch (1.59mm ± 0.79mm) from case for 10s Maximum

Reliability Information

Thermal Resistance	θ_{ja}	θ_{jc}
Ceramic DIP and FRIT Package	$80^oC/W$	$20^oC/W$
Flatpack Package	$70^oC/W$	$20^oC/W$

Maximum Package Power Dissipation (PD) at $+125^oC$
For TA = -55^oC to $+100^oC$ (Package Type D, F, K) 500mW
For TA = $+100^oC$ to $+125^oC$ (Package Type D, F, K) . . . . . Derate Linearity at $12mW/^oC$ to 200mW
Device Dissipation per Output Transistor. 100mW
For TA = Full Package Temperature Range (All Package Types)
Junction Temperature . . . . . $+175^oC$

TABLE 1. DC ELECTRICAL PERFORMANCE CHARACTERISTICS

PARAMETER	SYMBOL	CONDITIONS (NOTE 1)		GROUP A SUBGROUPS	TEMPERATURE	LIMITS MIN	LIMITS MAX	UNITS
Supply Current	IDD	VDD = 20V, VIN = VDD or GND		1	$+25^oC$	-	2	µA
				2	$+125^oC$	-	200	µA
		VDD = 18V, VIN = VDD or GND		3	-55^oC	-	2	µA
Input Leakage Current	IIL	VIN = VDD or GND	VDD = 20	1	$+25^oC$	-100	-	nA
				2	$+125^oC$	-1000	-	nA
			VDD = 18V	3	-55^oC	-100	-	nA
Input Leakage Current	IIH	VIN = VDD or GND	VDD = 20	1	$+25^oC$	-	100	nA
				2	$+125^oC$	-	1000	nA
			VDD = 18V	3	-55^oC	-	100	nA
Output Voltage	VOL15	VDD = 15V, No Load		1, 2, 3	$+25^oC$, $+125^oC$, -55^oC	-	50	mV
Output Voltage	VOH15	VDD = 15V, No Load (Note 3)		1, 2, 3	$+25^oC$, $+125^oC$, -55^oC	14.95	-	V
Output Current (Sink)	IOL5	VDD = 5V, VOUT = 0.4V		1	$+25^oC$	1.6	-	mA
Output Current (Sink)	IOL10	VDD = 10V, VOUT = 0.5V		1	$+25^oC$	5.0	-	mA
Output Current (Sink)	IOL15	VDD = 15V, VOUT = 1.5V		1	$+25^oC$	19	-	mA
Output Current (Source)	IOH5A	VDD = 5V, VOUT = 4.6V		1	$+25^oC$	-	-1.6	mA
Output Current (Source)	IOH5B	VDD = 5V, VOUT = 2.5V		1	$+25^oC$	-	-6.4	mA
Output Current (Source)	IOH10	VDD = 10V, VOUT = 9.5V		1	$+25^oC$	-	-5.0	mA
Output Current (Source)	IOH15	VDD = 15V, VOUT = 13.5V		1	$+25^oC$	-	-19	mA
N Threshold Voltage	VNTH	VDD = 10V, ISS = -10µA		1	$+25^oC$	-2.8	-0.7	V
P Threshold Voltage	VPTH	VSS = 0V, IDD = 10µA		1	$+25^oC$	0.7	2.8	V
Functional	F	VDD = 2.8V, VIN = VDD or GND		7	$+25^oC$	VOH > VDD/2	VOL < VDD/2	V
		VDD = 20V, VIN = VDD or GND		7	$+25^oC$			
		VDD = 18V, VIN = VDD or GND		8A	$+125^oC$			
		VDD = 3V, VIN = VDD or GND		8B	-55^oC			
Input Voltage Low (Note 2)	VIL	VDD = 5V, VOH > 4.5V, VOL < 0.5V		1, 2, 3	$+25^oC$, $+125^oC$, -55^oC	-	1.0	V
Input Voltage High (Note 2)	VIH	VDD = 5V, VOH > 4.5V, VOL < 0.5V		1, 2, 3	$+25^oC$, $+125^oC$, -55^oC	4.0	-	V
Input Voltage Low (Note 2)	VIL	VDD = 15V, VOH > 13.5V, VOL < 1.5V		1, 2, 3	$+25^oC$, $+125^oC$, -55^oC	-	2.5	V
Input Voltage High (Note 2)	VIH	VDD = 15V, VOH > 13.5V, VOL < 1.5V		1, 2, 3	$+25^oC$, $+125^oC$, -55^oC	12.5	-	V

NOTES:
1. All voltages referenced to device GND, 100% testing being implemented.
2. Go/No Go test with limits applied to inputs.
3. For accuracy, voltage is measured differentially to VDD. Limit is 0.050V max.

TABLE 2. AC ELECTRICAL PERFORMANCE CHARACTERISTICS

PARAMETER	SYMBOL	CONDITIONS (NOTE 1, 2)	GROUP A SUBGROUPS	TEMPERATURE	LIMITS MIN	LIMITS MAX	UNITS
Propagation Delay	TPHL TPLH	VDD = 5V, VIN = VDD or GND	9	+25°C	-	120	ns
			10, 11	+125°C, -55°C	-	162	ns
Transition Time	TTHL TTLH	VDD = 5V, VIN = VDD or GND	9	+25°C	-	80	ns
			10, 11	+125°C, -55°C	-	108	ns

NOTES:

1. CL = 50pF, RL = 200K, Input TR, TF < 20ns.
2. -55°C and +125°C limits guaranteed, 100% testing being implemented.

TABLE 3. ELECTRICAL PERFORMANCE CHARACTERISTICS

PARAMETER	SYMBOL	CONDITIONS	NOTES	TEMPERATURE	LIMITS MIN	LIMITS MAX	UNITS
Supply Current	IDD	VDD = 5V, VIN = VDD or GND	1, 2	-55°C, +25°C	-	1	µA
				+125°C	-	30	µA
		VDD = 10V, VIN = VDD or GND	1, 2	-55°C, +25°C	-	2	µA
				+125°C	-	60	µA
		VDD = 15V, VIN = VDD or GND	1, 2	-55°C, +25°C	-	2	µA
				+125°C	-	120	µA
Output Voltage	VOL	VDD = 5V, No Load	1, 2	+25°C, +125°C, -55°C	-	50	mV
Output Voltage	VOL	VDD = 10V, No Load	1, 2	+25°C, +125°C, -55°C	-	50	mV
Output Voltage	VOH	VDD = 5V, No Load	1, 2	+25°C, +125°C, -55°C	4.95	-	V
Output Voltage	VOH	VDD = 10V, No Load	1, 2	+25°C, +125°C, -55°C	9.95	-	V
Output Current (Sink)	IOL5	VDD = 5V, VOUT = 0.4V	1, 2	+125°C	1.2	-	mA
				-55°C	2.1	-	mA
Output Current (Sink)	IOL10	VDD = 10V, VOUT = 0.5V	1, 2	+125°C	3.5	-	mA
				-55°C	6.25	-	mA
Output Current (Sink)	IOL15	VDD = 15V, VOUT = 1.5V	1, 2	+125°C	13	-	mA
				-55°C	24	-	mA
Output Current (Source)	IOH5A	VDD = 5V, VOUT = 4.6V	1, 2	+125°C	-	-1.2	mA
				-55°C	-	-2.1	mA
Output Current (Source)	IOH5B	VDD = 5V, VOUT = 2.5V	1, 2	+125°C	-	-4.6	mA
				-55°C	-	-8.4	mA
Output Current (Source)	IOH10	VDD = 10V, VOUT = 9.5V	1, 2	+125°C	-	-3.5	mA
				-55°C	-	-6.25	mA
Output Current (Source)	IOH15	VDD =15V, VOUT = 13.5V	1, 2	+125°C	-	-13	mA
				-55°C	-	-24	mA
Input Voltage Low	VIL	VDD = 10V, VOH > 9V, VOL < 1V	1, 2	+25°C, +125°C, -55°C	-	2	V
Input Voltage High	VIH	VDD = 10V, VOH > 9V, VOL < 1V	1, 2	+25°C, +125°C, -55°C	8	-	V
Propagation Delay	TPHL TPLH	VDD = 10V	1, 2, 3	+25°C	-	70	ns
		VDD = 15V	1, 2, 3	+25°C	-	50	ns

TABLE 3. ELECTRICAL PERFORMANCE CHARACTERISTICS (Continued)

PARAMETER	SYMBOL	CONDITIONS	NOTES	TEMPERATURE	LIMITS		UNITS
					MIN	MAX	
Transition Time	TTHL TTLH	VDD = 10V	1, 2, 3	+25°C	-	40	ns
		VDD = 15V	1, 2, 3	+25°C	-	30	ns
Input Capacitance	CIN	Any Input	1, 2	+25°C	-	22.5	pF

NOTES:

1. All voltages referenced to device GND.
2. The parameters listed on Table 3 are controlled via design or process and are not directly tested. These parameters are characterized on initial design release and upon design changes which would affect these characteristics.
3. CL = 50pF, RL = 200K, Input TR, TF < 20ns.

TABLE 4. POST IRRADIATION ELECTRICAL PERFORMANCE CHARACTERISTICS

PARAMETER	SYMBOL	CONDITIONS	NOTES	TEMPERATURE	LIMITS		UNITS
					MIN	MAX	
Supply Current	IDD	VDD = 20V, VIN = VDD or GND	1, 4	+25°C	-	7.5	µA
N Threshold Voltage	VNTH	VDD = 10V, ISS = -10µA	1, 4	+25°C	-2.8	-0.2	V
N Threshold Voltage Delta	ΔVTN	VDD = 10V, ISS = -10µA	1, 4	+25°C	-	±1	V
P Threshold Voltage	VTP	VSS = 0V, IDD = 10µA	1, 4	+25°C	0.2	2.8	V
P Threshold Voltage Delta	ΔVTP	VSS = 0V, IDD = 10µA	1, 4	+25°C	-	±1	V
Functional	F	VDD = 18V, VIN = VDD or GND	1	+25°C	VOH > VDD/2	VOL < VDD/2	V
		VDD = 3V, VIN = VDD or GND					
Propagation Delay Time	TPHL TPLH	VDD = 5V	1, 2, 3, 4	+25°C	-	1.35 x +25°C Limit	ns

NOTES: 1. All voltages referenced to device GND.
2. CL = 50pF, RL = 200K, Input TR, TF < 20ns.
3. See Table 2 for +25°C limit.
4. Read and Record

TABLE 5. BURN-IN AND LIFE TEST DELTA PARAMETERS +25°C

PARAMETER	SYMBOL	DELTA LIMIT
Supply Current - MSI-1	IDD	± 0.2µA
Output Current (Sink)	IOL5	± 20% x Pre-Test Reading
Output Current (Source)	IOH5A	± 20% x Pre-Test Reading

TABLE 6. APPLICABLE SUBGROUPS

CONFORMANCE GROUP		MIL-STD-883 METHOD	GROUP A SUBGROUPS	READ AND RECORD
Initial Test (Pre Burn-In)		100% 5004	1, 7, 9	IDD, IOL5, IOH5A
Interim Test 1 (Post Burn-In)		100% 5004	1, 7, 9	IDD, IOL5, IOH5A
Interim Test 2 (Post Burn-In)		100% 5004	1, 7, 9	IDD, IOL5, IOH5A
PDA (Note 1)		100% 5004	1, 7, 9, Deltas	
Interim Test 3 (Post Burn-In)		100% 5004	1, 7, 9	IDD, IOL5, IOH5A
PDA (Note 1)		100% 5004	1, 7, 9, Deltas	
Final Test		100% 5004	2, 3, 8A, 8B, 10, 11	
Group A		Sample 5005	1, 2, 3, 7, 8A, 8B, 9, 10, 11	
Group B	Subgroup B-5	Sample 5005	1, 2, 3, 7, 8A, 8B, 9, 10, 11, Deltas	Subgroups 1, 2, 3, 9, 10, 11
	Subgroup B-6	Sample 5005	1, 7, 9	

TABLE 6. APPLICABLE SUBGROUPS (Continued)

CONFORMANCE GROUP	MIL-STD-883 METHOD	GROUP A SUBGROUPS	READ AND RECORD
Group D	Sample 5005	1, 2, 3, 8A, 8B, 9	Subgroups 1, 2 3

NOTE: 1. 5% Parameteric, 3% Functional; Cumulative for Static 1 and 2.

TABLE 7. TOTAL DOSE IRRADIATION

CONFORMANCE GROUPS	MIL-STD-883 METHOD	TEST		READ AND RECORD	
		PRE-IRRAD	POST-IRRAD	PRE-IRRAD	POST-IRRAD
Group E Subgroup 2	5005	1, 7, 9	Table 4	1, 9, Deltas	Table 4

TABLE 8. BURN-IN AND IRRADIATION TEST CONNECTIONS

FUNCTION	OPEN	GROUND	VDD	9V ± -0.5V	OSCILLATOR	
					50kHz	25kHz
Static Burn-In 1 (Note 1)	1, 2, 4, 5, 8, 9, 11, 12	3, 6, 7, 10, 13	14			
Static Burn-In 2 (Note 1)	1, 2, 4, 5, 8, 9, 11, 12	7	3, 6, 10, 13, 14			
Dynamic Burn-In (Note 2)	-	7	14	1, 2, 4, 5, 8, 9, 11, 12	3, 6, 10, 13	
Irradiation (Note 3)	1, 2, 4, 5, 8, 9, 11, 12	7	3, 6, 10, 13, 14			

NOTE:

1. Each pin except VDD and GND will have a series resistor of 10K ± 5%, VDD = 18V ± 0.5V
2. Each pin except VDD and GND will have a series resistor of 4.75K ± 5%; VDD = 18V ± 0.5V
3. Each pin except VDD and GND will have a series resistor of 47K ± 5%; Group E, Subgroup 2, sample size is 4 dice/wafer, 0 failures, VDD = 10V ± 0.5V

Typical Performance Characteristics

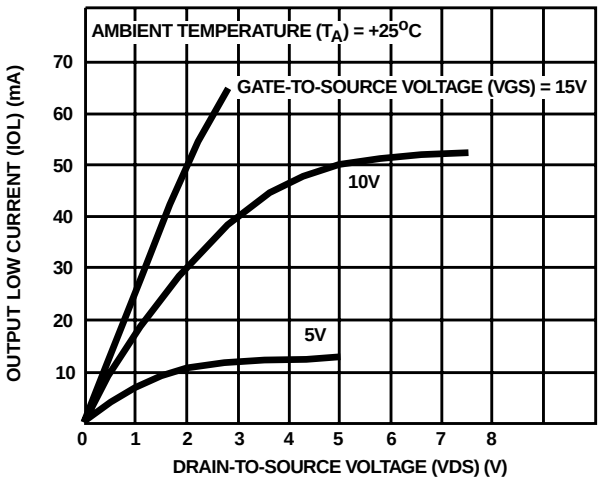


FIGURE 2. TYPICAL OUTPUT LOW (SINK) CURRENT CHARACTERISTICS

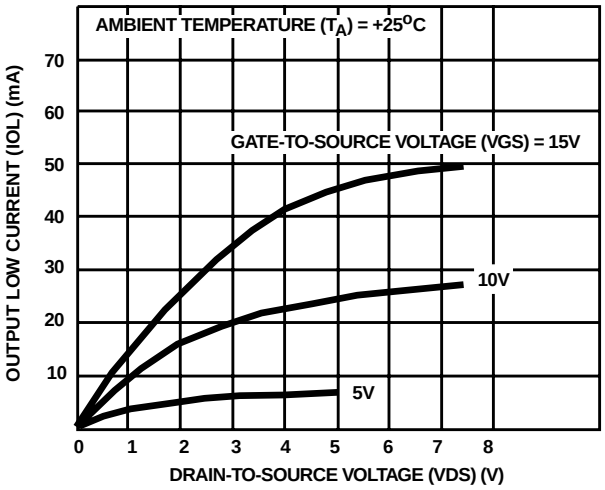


FIGURE 3. MINIMUM LOW (SINK) CURRENT CHARACTERISTICS

All Intersil semiconductor products are manufactured, assembled and tested under **ISO9000** quality systems certification.

Typical Performance Characteristics (Continued)

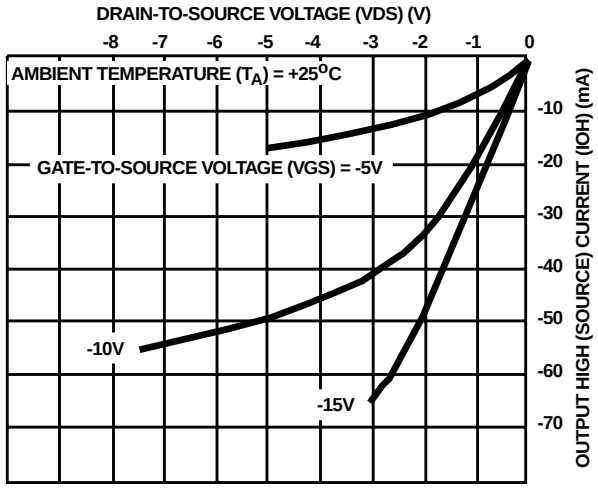


FIGURE 4. TYPICAL OUTPUT HIGH (SOURCE) CURRENT CHARACTERISTICS

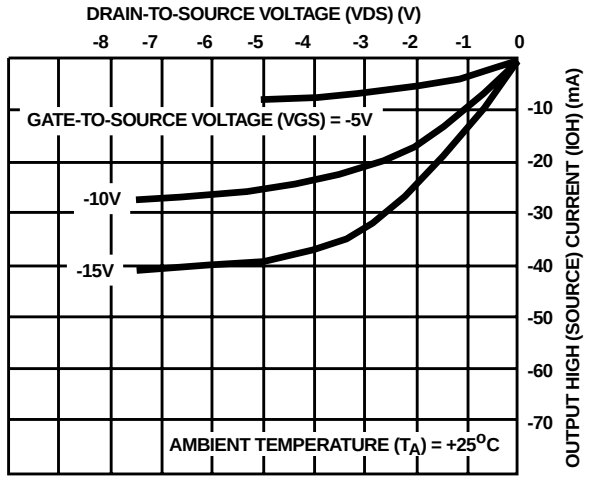


FIGURE 5. MINIMUM OUTPUT HIGH (SOURCE) CURRENT CHARACTERISTICS

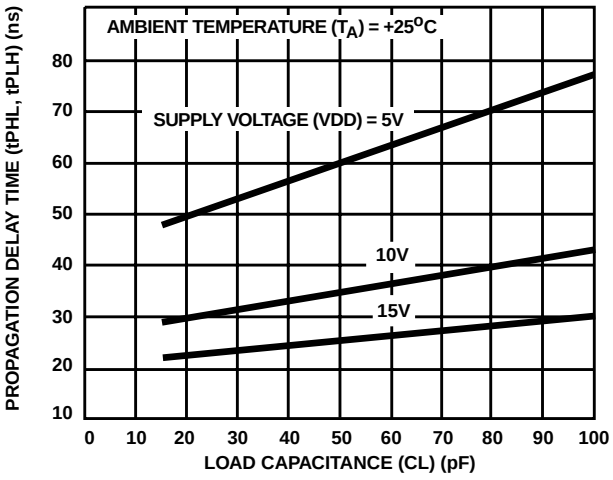


FIGURE 6. TYPICAL PROPAGATION DELAY TIME vs LOAD CAPACITANCE

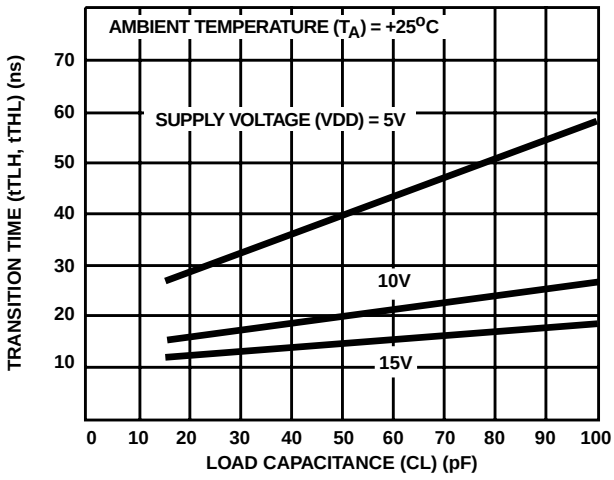


FIGURE 7. TYPICAL TRANSITION TIME vs LOAD CAPACITANCE

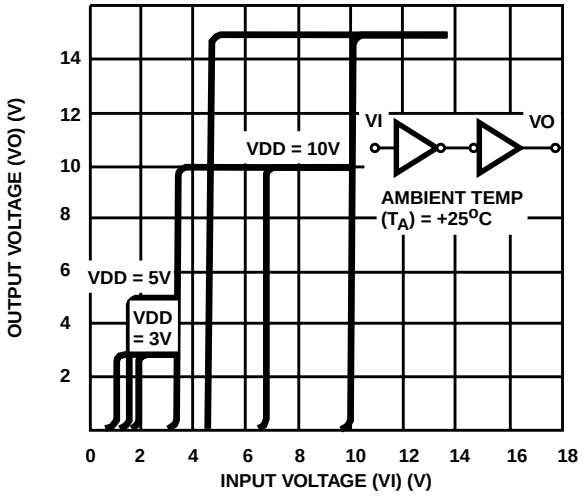


FIGURE 8. MINIMUM AND MAXIMUM TRANSFER CHARACTERISTICS - TRUE OUTPUT

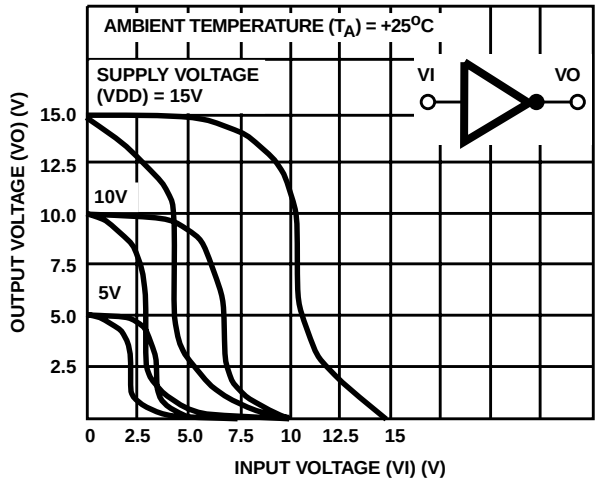


FIGURE 9. MINIMUM AND MAXIMUM TRANSFER CHARACTERISTICS - COMPLEMENT OUTPUT

Typical Performance Characteristics (Continued)

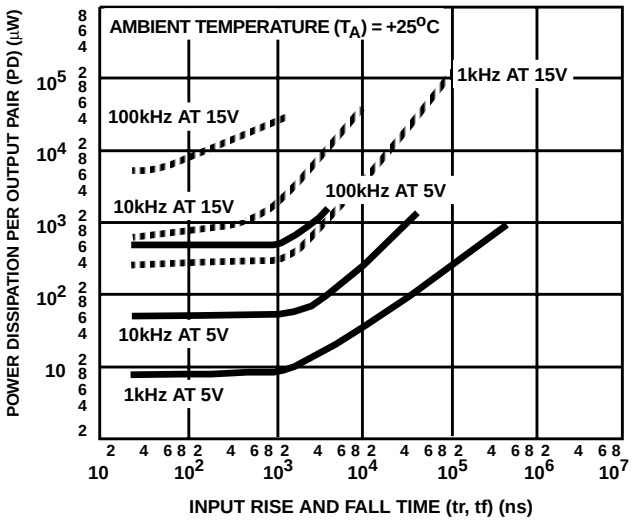


FIGURE 10. TYPICAL POWER DISSIPATION vs INPUT RISE AND FALL TIME PER OUTPUT PAIR

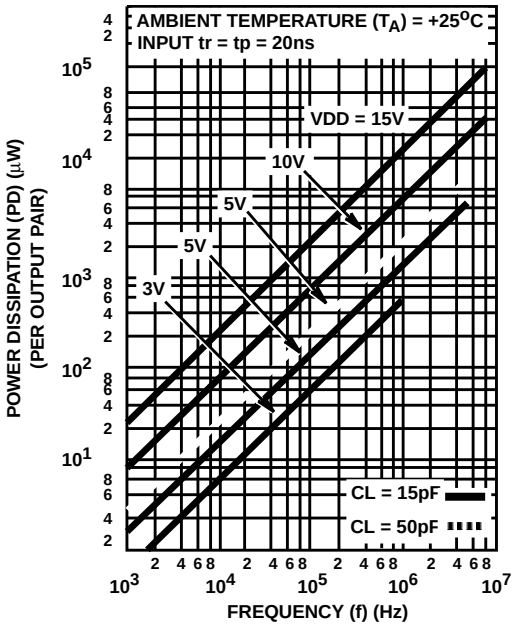
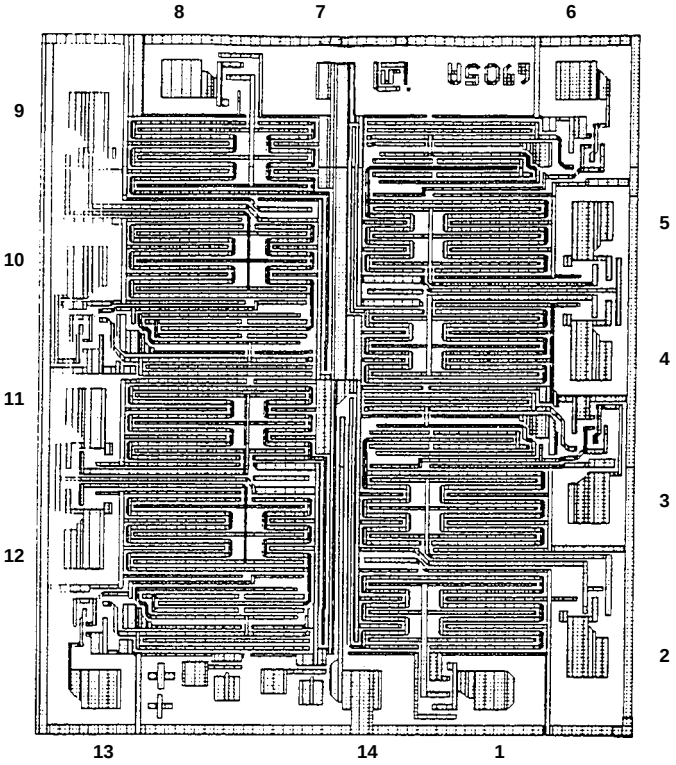


FIGURE 11. TYPICAL POWER DISSIPATION vs FREQUENCY PER OUTPUT PAIR

Chip Dimensions and Pad Layout



Dimensions in parentheses are in millimeters and are derived from the basic inch dimensions as indicated. Grid graduations are in mils (10^{-3} inch)

METALLIZATION: Thickness: 11kÅ – 14kÅ, AL.

PASSIVATION: 10.4kÅ - 15.6kÅ, Silane

BOND PADS: 0.004 inches X 0.004 inches MIN

DIE THICKNESS: 0.0198 inches - 0.0218 inches

DIE SIZE: X = 72 (69 - 77)
Y = 82 (79 - 87)